



2N5087 (3CG5087)

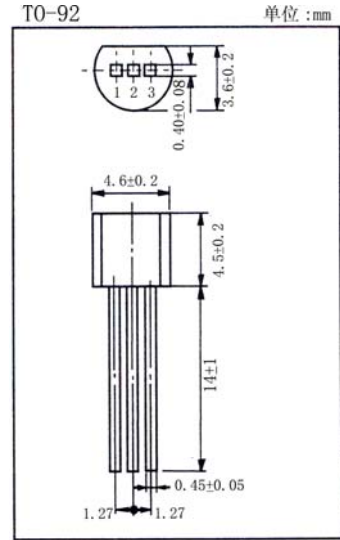
硅 PNP 半导体三极管/SILICON PNP TRANSISTOR

用途：用于集电极电流在 50mA 的低噪声、高增益的一般放大电路。

Purpose: This device is designed for low noise, high gain, general purpose amplifier applications at collector currents to 50mA.

极限参数/Absolute maximum ratings (Ta=25°C)

参数符号 Symbol	数值 Rating	单位 Unit
V <sub>CBO</sub>	-50	V
V <sub>CEO</sub>	-50	V
V <sub>EBO</sub>	-3	V
I <sub>C</sub>	-50	mA
P <sub>C</sub>	625	mW
T <sub>j</sub>	150	°C
T <sub>stg</sub>	-55~150	°C



引脚: 1. E 2. B 3. C

电性能参数/Electrical characteristics (Ta=25°C)

参数符号 Symbol	测试条件 Test condition	数值 Rating			单位 Unit
		最小值 Min	典型值 Typ	最大值 Max	
V <sub>CBO</sub>	I <sub>C</sub> =-100 μ A I <sub>E</sub> =0	-50			V
V <sub>CEO</sub>	I <sub>C</sub> =-1mA I <sub>B</sub> =0	-50			V
I <sub>EBO</sub>	V <sub>EB</sub> =-3V I <sub>C</sub> =0			-50	nA
I <sub>CBO</sub>	V <sub>CB</sub> =-10V I <sub>E</sub> =0			-10	nA
h <sub>FE(1)</sub>	V <sub>CE</sub> =-5V I <sub>C</sub> =-100 μ A	250		800	
h <sub>FE(2)</sub>	V <sub>CE</sub> =-5V I <sub>C</sub> =-10mA	250			
h <sub>FE(3)</sub>	V <sub>CE</sub> =-5V I <sub>C</sub> =-1mA	250			
V <sub>CE(sat)</sub>	I <sub>C</sub> =-10mA I <sub>B</sub> =-1mA			-0.3	V
V <sub>BE(on)</sub>	I <sub>C</sub> =-1mA V <sub>CE</sub> =-5V			-0.85	V
f <sub>T</sub>	I <sub>C</sub> =-500 μ A V <sub>CE</sub> =-5V f=20MHz	40			MHz
C <sub>cb</sub>	V <sub>CB</sub> =-5V I <sub>E</sub> =0 f=100KHz			4	pF
h <sub>fe</sub>	I <sub>C</sub> =-1mA V <sub>CE</sub> =-5V f=1KHz	250	900		
NF	I <sub>C</sub> =-100 μ A V <sub>CE</sub> =-5V R <sub>S</sub> =3K Ω f=1KHz		2		dB



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